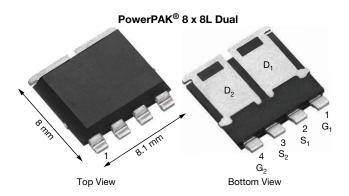


Vishay Siliconix

Automotive Dual N-Channel 40 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY			
V _{DS} (V)	40		
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0023		
I _D (A) per leg	100		
Configuration	Dual		

FEATURES

- TrenchFET® Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Fully lead (Pb)-free device
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





G ₁	G_2 G_2 G_2 G_2 G_2 G_3 G_4 G_5 G_5
N-Channel MOSFET	N-Channel MOSFET

ORDERING INFORMATION	
Package	PowerPAK 8 x 8L
Lead (Pb)-free and halogen-free	SQJQ936E (for detailed order number please see www.vishay.com/doc?79776)

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V_{DS}	40	V	
Gate-source voltage		V_{GS}	± 20		
Continuous drain current	T _C = 25 °C ^a	I-	100		
	T _C = 125 °C	- I _D	82		
Continuous source current (diode conduction) ^a		Is	68	А	
Pulsed drain current ^b		I _{DM}	400		
Single pulse avalanche current	L = 0.1 mH	I _{AS}	46.5		
Single pulse avalanche energy	L = U.T IIII	E _{AS}	110	mJ	
Maximum power dissipation	T _C = 25 °C	P _D	75	W	
	T _C = 125 °C	r _D	25		
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C	
Soldering recommendations (peak temperature) ^d			260		

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-ambient	PCB mount c	R_{thJA}	60	°C/W	
Junction-to-case (drain)		R_{thJC}	2	C/VV	

Notes

- a. Package limited
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- c. When mounted on 1" square PCB (FR4 material)
- d. See solder profile (www.vishay.com/doc?73257). The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection



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PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static				l			L	
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0$, $I_D = 250 \mu A$		40	-	-	\/	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$		3.0	3.5	V	
Gate-source leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA	
Zero gate voltage drain current		V _{GS} = 0 V	V _{DS} = 20 V	-	-	1		
	I _{DSS}	V _{GS} = 0 V	V _{DS} = 40 V, T _J = 125 °C	-	-	50	μΑ	
		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 175 °C	-	-	150	1 !	
On-state drain current a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 \text{ V}$	40	-	-	Α	
		V _{GS} = 10 V	I _D = 5 A	-	0.0019	0.0023	Ω	
Drain-source on-state resistance a	R _{DS(on)}	V _{GS} = 10 V	I _D = 5 A, T _J = 125 °C	-	-	0.0033		
		V _{GS} = 10 V	I _D = 5 A, T _J = 175 °C	-	-	0.0039		
Forward transconductance b	9 _{fs}	V _{DS} = 15 V, I _D = 15 A		-	120	=.	S	
Dynamic ^b								
Input capacitance	C _{iss}		0 V V _{DS} = 25 V, f = 1 MHz	-	4600	6600	pF	
Output capacitance	C _{oss}	$V_{GS} = 0 V$		-	1450	2030		
Reverse transfer capacitance	C _{rss}			-	120	170		
Total gate charge ^c	Qg			-	75	113	nC	
Gate-source charge c	Q_{gs}	$V_{GS} = 10 \text{ V}$	$V_{DS} = 20 \text{ V}, I_{D} = 15 \text{ A}$	-	22	-		
Gate-drain charge ^c	Q_{gd}			-	16	-		
Gate resistance	R_g	f = 1 MHz		0.9	1.9	2.6	Ω	
Turn-on delay time ^c	t _{d(on)}		$V_{DD} = 20 \text{ V}, R_L = 1.3 \Omega,$		18	27	ns ns	
Rise time ^c	t _r	V _{DD} =			24	36		
Turn-off delay time ^c	t _{d(off)}	$I_D \cong 15 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		-	34	51		
Fall time ^c	t _f				14	21		
Source-Drain Diode Ratings and Chara	acteristics ^b							
Pulsed current ^a	I _{SM}				-	272	Α	
Forward voltage	V _{SD}	I _F = 40 A, V _{GS} = 0 V		-	1	1.1	V	
Body diode reverse recovery time	t _{rr}	I _F = 40 A, di/dt = 100 A/μs		-	63	126	ns	
Body diode reverse recovery charge	Q _{rr}			-	86	172	nC	
Reverse recovery fall time	t _a			-	29	-	ns	
Reverse recovery rise time	t _b			-	33	-		
Body diode peak reverse recovery current	I _{RM(REC)}			-	2.6	-	Α	

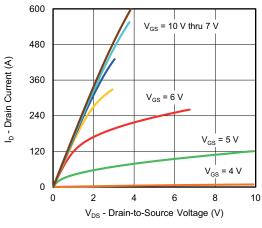
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

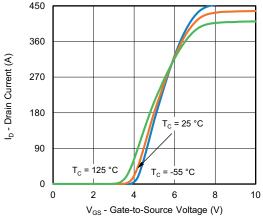
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



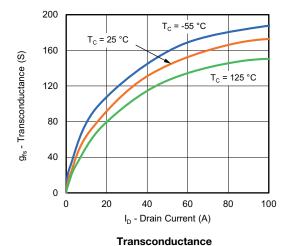
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

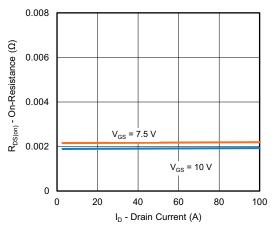


Output Characteristics

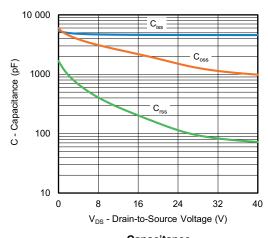


Transfer Characteristics

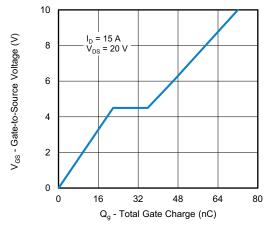




On-Resistance vs. Drain Current



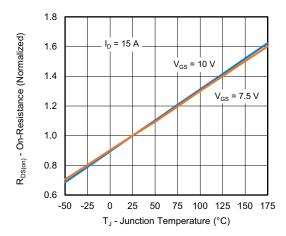
Capacitance



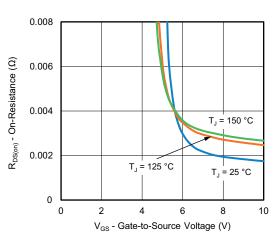
Gate Charge



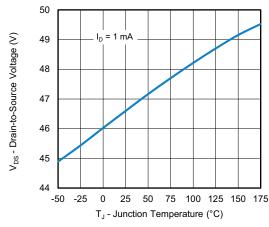
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



On-Resistance vs. Junction Temperature



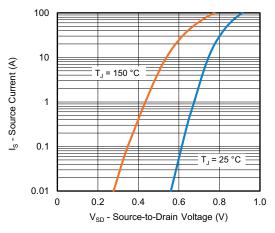
On-Resistance vs. Gate-to Source Voltage



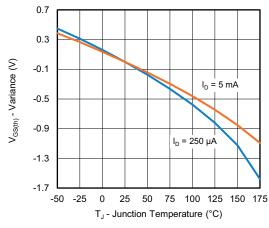
Drain Source Breakdown vs. Junction Temperature

Note

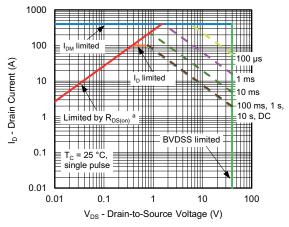
a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified



Source Drain Diode Forward Voltage



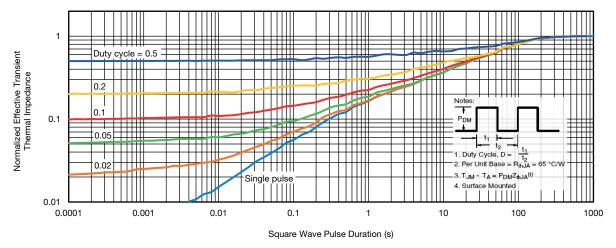
Threshold Voltage



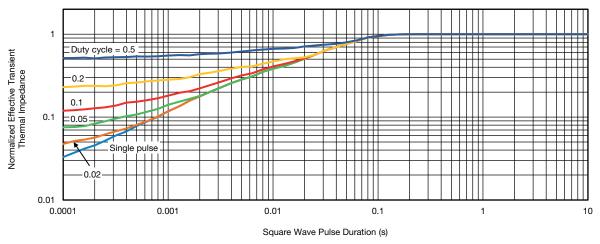
Safe Operating Area



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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